



ATTORNEY DOCKET NO.: CHOI 30-10-5-4-13

#9/AMDT
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10/22/02
VS
PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

TECHNOLOGY CENTER 2800

RECEIVED
OCT 18 2002

In re application of: Seungmoo Choi, et al.

Serial No.: 10/038,734

Filed: December 31, 2001

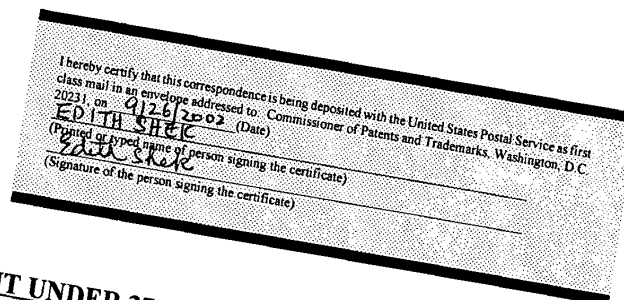
For: METHOD FOR FABRICATING MOS DEVICE WITH
HALO IMPLANTED REGION

Grp./A.U.: 2812

Examiner: Booth, Richard A.

Honorable Commissioner of Patents
Washington, D.C. 20231

Sir:



AMENDMENT UNDER 37 C.F.R. § 1.111

In response to the Examiner's Action mailed June 27, 2002, please amend the above-identified application as follows:

IN THE SPECIFICATION:

- (1) Please amend the paragraph at page 5, lines 17-23 as follows:

It should be readily appreciated that n-channel transistors may be similarly formed, but with an n-type source 24, an n-type channel 30, an n-type drain 26, and lightly-doped p-type halo implants

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